

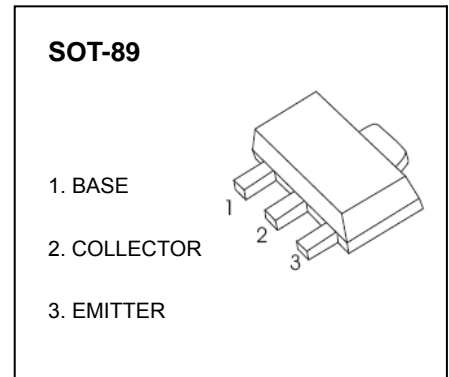
## Plastic-Encapsulate NPN Transistors

### FEATURES

- High current: 1A
- PD Power Dissipation:500mW

### MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	32	V
V <sub>CEO</sub>	Collector-Emitter Voltage	20	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current -Continuous	1	A
P <sub>C</sub>	Collector Power Dissipation	500	mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~150	°C



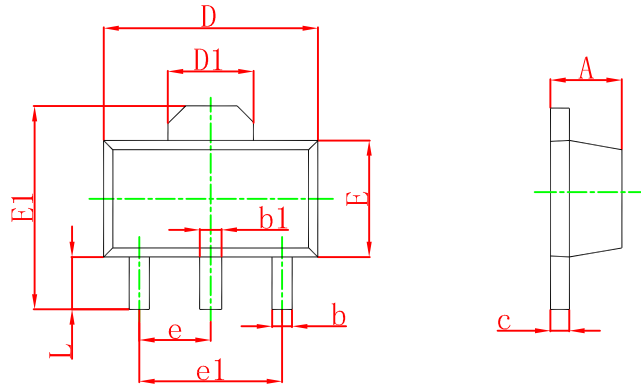
### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =100μA, I <sub>E</sub> =0	32			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0	20			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =100μA, I <sub>C</sub> =0	5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =25V, I <sub>E</sub> =0			0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0			0.1	μA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =500mA	85		375	
	h <sub>FE(2)</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =1A	60			
	h <sub>FE(3)</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =5mA	50			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =1A, I <sub>B</sub> =100mA			0.5	V
Base-emitter voltage	V <sub>BE1</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =5mA		0.62		V
	V <sub>BE2</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> =1A			1	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA, f=100MHz	40			MHz

### CLASSIFICATION OF h<sub>FE(1)</sub>

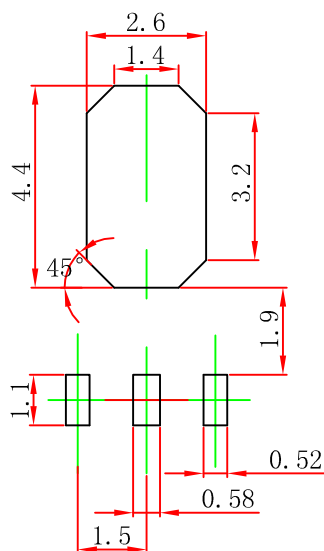
Rank	BC868	BC868-10	BC868-16	BC868-25
Range	85-375	85-160	100-250	160-375
Marking	CAC	CBC	CCC	CDC

SOT-89 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047

Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.

## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [Bipolar Transistors - BJT category](#):*

*Click to view products by [Shikues manufacturer](#):*

Other Similar products are found below :

[619691C](#) [MCH4017-TL-H](#) [MJ15024/WS](#) [MJ15025/WS](#) [BC546/116](#) [BC556/FSC](#) [BC557/116](#) [BSW67A](#) [HN7G01FU-A\(T5L,F,T](#)  
[NJVMJD148T4G](#) [NSVMMBT6520LT1G](#) [NTE187A](#) [NTE195A](#) [NTE2302](#) [NTE2330](#) [NTE2353](#) [NTE316](#) [IMX9T110](#) [NTE63](#) [NTE65](#)  
[C4460](#) [SBC846BLT3G](#) [2SA1419T-TD-H](#) [2SA1721-O\(TE85L,F\)](#) [2SA1727TLP](#) [2SA2126-E](#) [2SB1202T-TL-E](#) [2SB1204S-TL-E](#) [2SC5488A-](#)  
[TL-H](#) [2SD2150T100R](#) [SP000011176](#) [FMC5AT148](#) [2N2369ADCSM](#) [2SB1202S-TL-E](#) [2SC2412KT146S](#) [2SC4618TLN](#) [2SC5490A-TL-H](#)  
[2SD1816S-TL-E](#) [2SD1816T-TL-E](#) [CMXT2207 TR](#) [CPH6501-TL-E](#) [MCH4021-TL-E](#) [BC557B](#) [TTC012\(Q\)](#) [BULD128DT4](#) [JANTX2N3810](#)  
[Jantx2N5416](#) [US6T6TR](#) [KSF350](#) [068071B](#)